SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

DGG OR DGV PACKAGE

- Member of the Texas Instruments Widebus™ Family
- TI-OPC™ Circuitry Limits Ringing on **Unevenly Loaded Backplanes**
- **OEC™** Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference
- **Bidirectional Interface Between GTLP** Signal Levels and LVTTL Logic Levels
- Split LVTTL Port Provides a Feedback Path for Control and Diagnostics Monitoring
- LVTTL Interfaces Are 5-V Tolerant
- **High-Drive GTLP Open-Drain Outputs** (100 mA)
- LVTTL Outputs (-24 mA/24 mA)
- Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for **Optimal Data-Transfer Rate and Signal** Integrity in Distributed Loads
- Ioff, Power-Up 3-State, and BIAS VCC **Support Live Insertion**
- Distributed V_{CC} and GND Pins Minimize **High-Speed Switching Noise**
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22**
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

(TOP VIEW) IMODE1 48 ∏ IMODE0 47 BIAS VCC Al1 2 AO1 [] 3 46 🛮 B1 GND 45 | GND 114 44 **∏** OEAB Al2 | 15 AO2 6 43 T B2 42 TERC V_{CC} []7 41 OEAB AI3 AO3 [] 9 40 ∏ B3 GND ∏10 39 | GND AI4 [] 11 38 CLKAB/LEAB AO4 37 ∏ B4 12 AO5 ∏ 13 36 ∏ B5 AI5 Π 35 CLKBA/LEBA 14 GND 15 34 ∏ GND AO6 16 33 🛮 B6 Al6 17 32 | OEBA V_{CC} 18 31 V_{CC} AO7 П 19 30 **∏** B7 29 LOOPBACK 20 GND 21 28 | GND AO8 1 22 27 | B8 AI8 23 26 V_{RFF} 25 OMODE1 OMODE0 I 24

description

The SN74GTLP2033 is a high-drive, 8-bit, three-wire registered transceiver that provides inverted LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. The device allows for transparent, latched, and flip-flop modes of data transfer with separate LVTTL input and LVTTL output pins, which provides a feedback path for control and diagnostics monitoring, the same functionality as the SN74FB2033. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC™ circuitry, and TI-OPC™ circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω .



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

OEC, TI-OPC, and Widebus are trademarks of Texas Instruments



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

description (continued)

GTLP is the Texas Instruments derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLP2033 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels. For information on using GTLP devices in FB+/BTL applications, refer to TI application reports, *Texas Instruments GTLP Frequently Asked Questions*, literature number SCEA019, and *GTLP in BTL Applications*, literature number SCEA017.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and can be directly driven by TTL or 5-V CMOS devices. V_{REF} is the B-port differential input reference voltage.

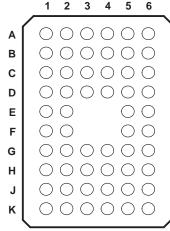
This device is fully specified for live-insertion applications using I_{off} , power-up 3-state, and BIAS V_{CC} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V_{CC} circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between low and high adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OEAB} should be tied to V_{CC} through a pullup resistor and OEAB and OEBA should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

GQL PACKAGE (TOP VIEW)



terminal assignments

	1	2	3	4	5	6
Α	IMODE1	NC	NC	NC	NC	IMODE0
В	AO1	Al1	GND	GND	BIAS V _{CC}	B1
С	AO2	Al2	Vcc	ERC	OEAB	B2
D	AO3	Al3	GND	GND	OEAB	В3
Е	AO4	Al4			CLKAB/LEAB	B4
F	AO5	AI5			CLKBA/LEBA	B5
G	AO6	Al6	GND	GND	OEBA	B6
Н	AO7	AI7	Vcc	Vcc	LOOPBACK	B7
J	AO8	Al8	GND	GND	V _{REF}	B8
K	OMODE0	NC	NC	NC	NC	OMODE1

NC = No internal connection



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

ORDERING INFORMATION

TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 85°C	TSSOP – DGG	Tape and reel	SN74GTLP2033DGGR	GTLP2033
	TVSOP - DGV	Tape and reel	SN74GTLP2033DGVR	GT2033
	VFBGA – GQL	Tape and reel	SN74GTLP2033GQLR	GR033

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

functional description

The SN74GTLP2033 is a high-drive (100 mA), 8-bit, three-wire registered transceiver containing D-type latches and D-type flip-flops for data-path operation in the transparent, latched, or flip-flop modes. Data transmission is complementary, with inverted AI data going to the B port and inverted B data going to AO. The split LVTTL AI and AO provides a feedback path for control and diagnostics monitoring.

The logic element for data flow in each direction is configured by two mode (IMODE1 and IMODE0 for B to A, OMODE1 and OMODE0 for A to B) inputs as a buffer, D-type flip-flop, or D-type latch. When configured in the buffer mode, the inverted input data appears at the output port. In the flip-flop mode, data is stored on the rising edge of the appropriate clock (CLKAB/LEAB or CLKBA/LEBA) input. In the latch mode, the clock inputs serve as active-high transparent latch enables.

Data flow in the B-to-A direction, regardless of the logic element selected, is further controlled by the LOOPBACK input. When LOOPBACK is low, B-port data is the B-to-A input. When LOOPBACK is high, the output of the selected A-to-B logic element (prior to inversion) is the B-to-A input.

The AO enable/disable control is provided by OEBA. When OEBA is low or when V_{CC} is less than 1.5 V, AO is in the high-impedance state. When OEBA is high, AO is active (high or low logic levels).

The B port is controlled by OEAB and $\overline{\text{OEAB}}$. If OEAB is low, $\overline{\text{OEAB}}$ is high, or V_{CC} is less than 1.5 V, the B port is inactive. If OEAB is high and $\overline{\text{OEAB}}$ is low, the B port is active.

The A-to-B and B-to-A logic elements are active, regardless of the state of their associated outputs. The logic elements can enter new data (in flip-flop and latch modes) or retain previously stored data while the associated outputs are in the high-impedance (AO) or inactive (B port) states.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

Function Tables

FUNCTION/MODE

				INPUTS				CUITDUIT	MODE	
OEBA	OEAB	OEAB	OMODE1	OMODE0	IMODE1	IMODE0	LOOPBACK	OUTPUT	MODE	
L	L	Χ	Х	Х	Х	Х	X	7	la alatha	
L	X	Н	Χ	Χ	Χ	Χ	X	Z	Isolation	
Х	Н	L	L	L	Х	Х	X		Buffer	
Х	Н	L	L	Н	Χ	Χ	X	Inverted AI to B	Flip-flop	
Х	Н	L	Н	Χ	Χ	Χ	X		Latch	
Н	L	Χ	Х	Х	L	L	L	leavested B to AO	D. #	
Н	Χ	Н	Χ	Χ	L	L	L	Inverted B to AO	Buffer	
Н	L	Χ	Х	Х	L	Н	L	leavested B to AO	El'a dan	
Н	Χ	Н	Χ	Χ	L	Н	L	Inverted B to AO	Flip-flop	
Н	L	Χ	Х	Х	Н	Х	L	Learning I B to A O	Latab	
Н	Χ	Н	Χ	Χ	Н	Χ	L	Inverted B to AO	Latch	
Н	L	Χ	Χ	Χ	L	L	Н	A14- A0	D. #	
Н	Χ	Н	Χ	Χ	L	L	Н	AI to AO	Buffer	
Н	L	Χ	Χ	Χ	L	Н	Н	A1 40 A O	Flip floor	
Н	Χ	Н	Χ	Χ	L	Н	Н	AI to AO	Flip-flop	
Н	L	X	Х	Х	Н	Х	Н	Al to AO	Latah	
Н	Χ	Н	Х	Χ	Н	X	Н	AI to AO	Latch	
Н	Н	L	Х	Х	Х	Х	L	Inverted AI to B, Inverted B to AO	Transparent with feedback path	

ENABLE/DISABLE

	INPUTS	OUTI	PUTS					
OEBA	OEAB	OEAB	AO	В				
L	Χ	Χ	Z					
Н	Χ	Χ	Active					
Х	L	L		Z				
Х	L	Н		Z				
Х	Н	L		Active				
Х	Н	Н		Z				

BUFFER

INPUT	OUTPUT
L	Н
Н	L

LATCH

INPU	OUTDUT	
CLK/LE	OUTPUT	
Н	L	Н
Н	Н	L
L	X	Q ₀



SN74GTLP2033 8-BIT LVTTL-TO-GTLP ADJUSTABLE-EDGE-RATE REGISTERED TRANSCEIVER WITH SPLIT LYTTL PORT AND FEEDBACK PATH SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

Function Tables (Continued)

LOOPBACK

LOOPBACK	Q†
L	B port
Н	Point P‡

[†]Q is the input to the B-to-A logic element.

SELECT

INPUTS MODE1 MODE0		SELECTED LOGIC
		ELEMENT
L	L	Buffer
L	Н	Flip-flop
Н	Χ	Latch

FLIP-FLOP

INPU'	TS	OUTDUT		
CLK/LE	DATA	OUTPUT		
L	Х	Q ₀		
1	L	Н		
1	Н	L		

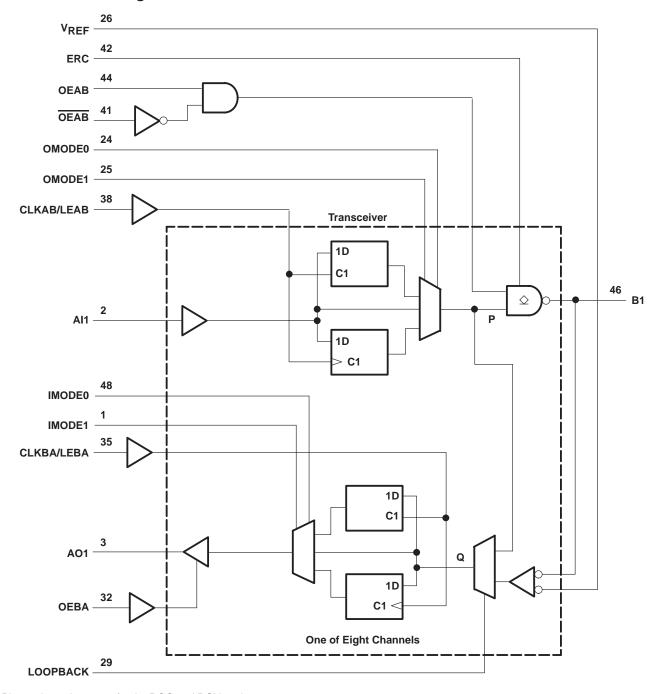
B-PORT EDGE-RATE CONTROL (ERC)

INPUT ERC	OUTPUT B-PORT
LOGIC LEVEL	EDGE RATE
Н	Slow
L	Fast

[‡]P is the output of the A-to-B logic element (see functional block diagram).

SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

functional block diagram



Pin numbers shown are for the DGG and DGV packages.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} and BIAS V_{CC}	.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V _O	
(see Note 1): AO port	
B port	V to 4.6 V
Current into any output in the low state, IO: AO port	48 mA
B port	200 mA
Current into any A-port output in the high state, IO (see Note 2)	48 mA
Continuous current through each V _{CC} or GND	
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	70°C/W
DGV package	
GQL package	
Storage temperature range, T _{stq} –65°C	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

recommended operating conditions (see Notes 4 through 7)

			MIN	NOM	MAX	UNIT	
V _{CC} , BIAS V _{CC}	Supply voltage		3.15	3.3	3.45	V	
.,		GTL	1.14	1.2	1.26	V	
VTT	Termination voltage	GTLP	1.35	1.5	1.65		
V	Defended welling	GTL	0.74	0.8	0.87	.,	
V_{REF}	Reference voltage	GTLP	0.87	1	1.1	V	
VI	Lament and the ma	B port			VTT	V	
	Input voltage	Except B port and VREF		Vcc	5.5		
VIH	High-level input voltage	B port	V _{REF} +0.05			V	
		Except B port	2				
V		B port			V _{REF} -0.05	.,	
VIL	Low-level input voltage	Except B port			0.8	V	
l _{IK}	Input clamp current				-18	mA	
loh	High-level output current	AO			-24	mA	
		AO			24		
lOL	Low-level output current	B port			100	mA	
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V	
Δt/ΔV _{CC}	Power-up ramp rate		20			μs/V	
T _A	Operating free-air temperature		-40		85	°C	

- NOTES: 4. All unused control and B-port inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
 - 5. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS V_{CC} = 3.3 V first, I/O second, and V_{CC} = 3.3 V last, because the BIAS V_{CC} precharge circuitry is disabled when any V_{CC} pin is connected. The control and V_{REF} inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable but, generally, GND is connected first.
 - 6. V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances if the dc recommended I_{OL} ratings are not exceeded.
 - 7. V_{REF} can be adjusted to optimize noise margins, but normally is two-thirds V_{TT}. TI-OPC circuitry is enabled in the A-to-B direction and is activated when V_{TT} > 0.7 V above V_{REF}. If operated in the A-to-B direction, V_{REF} should be set to within 0.6 V of V_{TT} to minimize current drain.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

electrical characteristics over recommended operating free-air temperature range for GTLP (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT		
٧ıK		$V_{CC} = 3.15 V,$	I _I = -18 mA			-1.2	V		
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0.2					
V_{OH}	AO	V 245 V	$I_{OH} = -12 \text{ mA}$	2.4			V		
		V _{CC} = 3.15 V	$I_{OH} = -24 \text{ mA}$	2					
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	$I_{OL} = 100 \mu\text{A}$			0.2			
	AO	V _{CC} = 3.15 V	$I_{OL} = 12 \text{ mA}$			0.4			
\/a:		VCC = 3.13 V	$I_{OL} = 24 \text{ mA}$			0.5	V		
VOL			$I_{OL} = 10 \text{ mA}$			0.2	V		
	B port	V _{CC} = 3.15 V	$I_{OL} = 64 \text{ mA}$			0.4			
			$I_{OL} = 100 \text{ mA}$			0.55			
ı _l ‡	Al and control inputs	V _{CC} = 3.45 V,	V _I = 0 or 5.5 V			±10	μΑ		
. +	AO	V _{CC} = 3.45 V,	$V_0 = 0 \text{ to } 5.5 \text{ V}$			±10			
loz‡	B port	V_{CC} = 3.45 V, V_{REF} within 0.6 V of V_{TT} ,	V _O = 0 to 2.3 V			±10	μΑ		
		V _{CC} = 3.45 V, I _O = 0,	Outputs high			40			
ICC	AO or B port	V _I (A-port or control input) = V _{CC} or GND,	Outputs low			40	mA		
		V_I (B port) = V_{TT} or GND	Outputs disabled			40			
ΔlCC§		V _{CC} = 3.45 V, One AI or control input at V _C . Other AI or control inputs at V _{CC} or GND	C - 0.6 V,			1.5	mA		
_	AI	V 0.45V 0							
Ci	Control inputs	V _I = 3.15 V or 0			3.5	5.5	pF		
Co	AO	V _O = 3.15 V or 0			5	6	pF		
C _{io}	B port	V _O = 1.5 V or 0	_		8.5	10	pF		

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

hot-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS					
loff	$V_{CC} = 0$,	V_I or $V_O = 0$ to 5.5 V			10	μΑ	
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to 3 V},$	OEBA = V _{CC}		±30	μΑ	
lozpd	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	OEBA = V _{CC}		±30	μΑ	

live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITION	S	MIN	MAX	UNIT			
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 1.5 V		10	μΑ			
lozpu	$V_{CC} = 0$ to 1.5 V, BIAS V		±30	μΑ					
lozpd	V _{CC} = 1.5 V to 0, BIAS \	$C_{CC} = 1.5 \text{ V}$ to 0, BIAS $V_{CC} = 0$, $V_{O} = 0.5 \text{ V}$ to 1.5 V, $\overline{OEAB} = 0$ and $OEAB = V_{CC}$							
Icc	V _{CC} = 0 to 3.15 V	DIA 0 1/2 0 45 1/4	V (D mart) 0.15 4.5 V		5	mA			
(BIAS V _{CC})	V _{CC} = 3.15 V to 3.45 V	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	VO (Β port) = 0 to 1.5 V		10	μΑ			
Vo	$V_{CC} = 0$,	BIAS $V_{CC} = 3.3 V$,	IO = 0	0.95	1.05	V			
lo	$V_{CC} = 0$,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V}$,	V _O (B port) = 0.6 V	-1	·	μΑ			



[‡] For I/O ports, the parameter IOZ includes the input leakage current.

[§] This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.

SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
fclock	Clock frequency			175	MHz
t _W	Pulse duration	CLKAB/LEAB or CLKBA/LEBA	2.8		ns
		Al before CLKAB↑	1.1		
		Al before CLKBA↑	1.4		
_		B before CLKBA↑	1		
t _{su}	Setup time	Al before LEAB↓	1.6		ns
		Al before LEBA↓	2.1		
		B before LEBA↓	2.2		
		Al after CLKAB↑	0.3		
		Al after CLKBA↑	0.2		
		B after CLKBA↑	0.6		
^t h	Hold time	Al after LEAB↓	0.3		ns
		Al after LEBA↓	0		
		B after LEBA↓	0		



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	MIN	TYP‡ MAX	UNIT
f _{max}				175		MHz
tPLH	Al	_	-	3	7.4	
^t PHL	(buffer)	В	Slow	3	7.1	ns
t _{PLH}	Al		- .	2	5.9	
^t PHL	(buffer)	В	Fast	2	5.8	ns
^t PLH	В	100		1	5.7	
^t PHL	(buffer)	AO	_	1	5	ns
^t PLH	LEAB		Class	4.2	8.6	20
^t PHL	(latch mode)	В	Slow	3.2	7.7	ns
^t PLH	LEAB	В	Fast	3.2	7.6	no
^t PHL	(latch mode)	В	rasi	2.8	6.7	ns
^t PLH	LEAB	AO		2	7	no
^t PHL	(latch mode)	AO	_	1.8	6.3	ns
^t PLH	LEBA	AO		1	5.7	nc
^t PHL	(latch mode)	AO	_	1	4.7	ns
^t PLH	OEAB	В	Slow	3.8	7.5	ns
^t PHL	OLAB	Ь	Slow	3.1	7	115
t _{PLH}	OEAB	В	Fast	2.5	6	ns
^t PHL	OLAB	Ь	FaSi	2.5	6	115
t _{PLH}	OEAB	В	Slow	3.5	7.5	ns
^t PHL	OLAB	Ь	Slow	3	7.2	115
t _{PLH}	OEAB	В	Fast	2.5	6	ns
^t PHL	OLAB	Ь	rast	2.5	6	113
^t PZH	OEBA	AO	_	1	4.7	ns
t _{PZL}	OLDA	٨٥	_	1	3.4	113
^t PHZ	OEBA	AO		1	5.2	ns
^t PLZ	OLDA	٨٥	_	1	4.9	113
^t PLH	CLKAB	В	Slow	4.4	8.8	ns
^t PHL	(flip-flop mode)	5	Glow	3.6	8.1	113
^t PLH	CLKAB	В	Fast	3.2	7.2	ns
^t PHL	(flip-flop mode)	5	1 431	3.1	6.9	110
t _{PLH}	CLKAB	AO	_	2	6.9	ns
t _{PHL}	(flip-flop mode)	710		1.8	6.4	110
t _{PLH}	CLKBA	AO	_	1	5.6	ns
^t PHL	(flip-flop mode)	710		1	4.9	110
^t PLH	OMODE	В	Slow	3.8	8.7	ns
^t PHL	0.110BE		Clow	3.2	8.2	110
^t PLH	OMODE	В	Fast	2.7	7.2	ns
^t PHL	O.MODE		1 431	2.7	7.2	
t _{PLH}	IMODE	AO	_	1	5.6	ns
t _{PHL}		1.5		1	4.6	_

[†] Slow (ERC = H) and Fast (ERC = L)

[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



SN74GTLP2033

8-BIT LVTTL-TO-GTLP ADJUSTABLE-EDGE-RATE REGISTERED TRANSCEIVER WITH SPLIT LVTTL PORT AND FEEDBACK PATH

SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$ for GTLP (see Figure 1) (continued)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	MIN	TYP‡	MAX	UNIT
^t PLH	1.000004014	40		2.5	6.2	6.2	
t _{PHL}	LOOPBACK	AO	-	2	5	5	ns
t _{PLH}	Al	40		1	5.6	5.6	
t _{PHL}	(loopback high)	AO	-	1	5	5	ns
	Dies ties Deserted outside (00	Slow		2.8			
t _r	Rise time, B-port outputs (20	Fast		1.5 n			
	Rise time, AO (10% to 90%)				3.5		
	- H :	2(4 . 000()	Slow		3		
t _f	Fall time, B-port outputs (80°	Fall time, \overline{B} -port outputs (80% to 20%)			1.8		
	Fall time, AO (90% to 10%)				1.5		

[†] Slow (ERC = H) and Fast (ERC = L)

skew characteristics over recommended ranges of supply voltage and operating free-air temperature (see Figure 1)§

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	MIN TYP‡	MAX	UNIT
t _{sk(LH)} ¶	Al	В	Slow	0.5	1	20
t _{sk(HL)} ¶	Al	В	Slow	0.5	1	ns
t _{sk(LH)} ¶	Al	В	Fast	0.4	0.9	ns
t _{sk(HL)} ¶	Al	В	газі	0.4	0.9	115
$t_{sk(LH)}^{\P}$	CLKAB/LEAB	В	Slow	0.5	1	ns
t _{sk(HL)} ¶	CLNAD/LLAD	В	Slow	0.5	1	115
t _{sk(LH)} ¶	CLKAB/LEAB	В	Fast	0.4	0.9	ns
t _{sk(HL)} ¶	CLNAD/LEAD	В	газі	0.4	0.9	115
	Al	В	Slow	1.4	2	
$t_{sk(t)}\P$	Al	В	Fast	0.6	1.4	ns
'SK(t)"	CLKAR/LEAR	В	Slow	1.8	2.5	113
	CLKAB/LEAB	5	Fast	0.9	1.8	

[†] Slow (ERC = L) and Fast (ERC = H)



[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

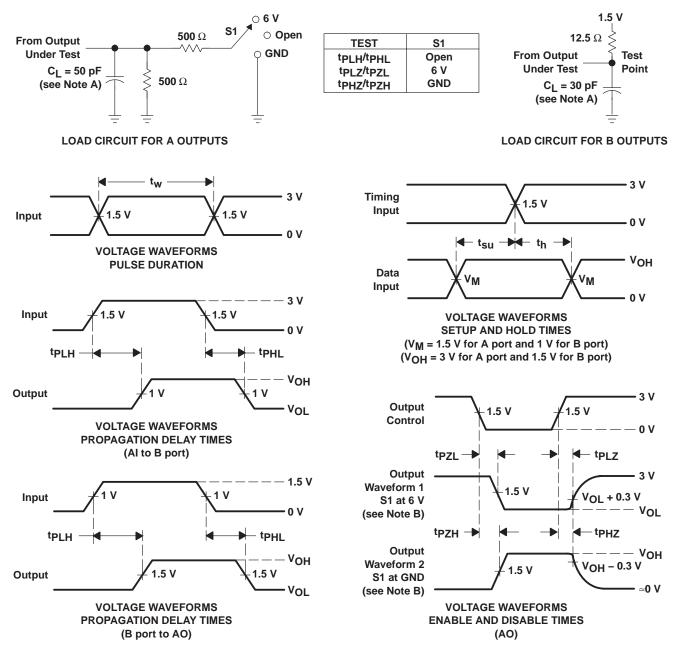
[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

[§] Actual skew values between the GTLP outputs could vary on the backplane due to the loading and impedance seen by the device.

[¶] t_{sk(LH)}/t_{sk(HL)} and t_{sk(t)} – Output-to-output skew is defined as the absolute value of the difference between the actual propagation delay for all outputs with the same packaged device. The specifications are given for specific worst-case V_{CC} and temperature and apply to any outputs switching in the same direction either high to low [t_{sk(HL)}] or low to high [t_{sk(LH)}] or in opposite directions, both low to high and high to low [t_{sk(t)}].

SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \approx 10 MHz, Z_O = 50 Ω , $t_f \approx$ 2 ns. $t_f \approx$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application is probably a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer to better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

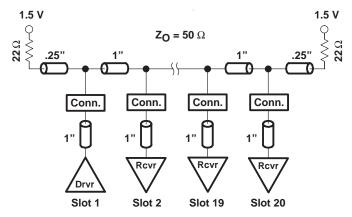


Figure 2. High-Drive Test Backplane

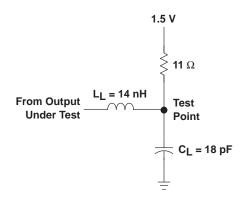


Figure 3. High-Drive RLC Network



SN74GTLP2033 8-BIT LVTTL-TO-GTLP ADJUSTABLE-EDGE-RATE REGISTERED TRANSCEIVER WITH SPLIT LYTTL PORT AND FEEDBACK PATH SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended operating conditions for the bus transceiver function (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE†	түр‡	UNIT
t _{PLH}	Al		- C	4.7	
t _{PHL}	(buffer)	В	Slow	5	ns
^t PLH	Al		Fort	3.7	
^t PHL	(buffer)	В	Fast	4	ns
^t PLH	LEAB		01	5.5	
^t PHL	(latch mode)	В	Slow	5.8	ns
^t PLH	LEAB		Fort	4.6	
^t PHL	(latch mode)	В	Fast	4.8	ns
^t PLH	CLKAB	D	Class	5.8	
^t PHL	(flip-flop mode)	В	Slow	6	ns
^t PLH	CLKAB	В	Fast	4.9	20
^t PHL	(flip-flop mode)	D	rasi	4.9	ns
^t PLH	OMODE	В	Slow	5.5	
^t PHL	OIVIODE	В	Slow	5.7	ns
t _{PLH}	OMODE	В	Foot	4.5	20
^t PHL	OIMODE	D	Fast	4.7	ns
	Rise time, B-port outputs (20)0/ to 900/)	Slow	1.8	20
t _r	Rise time, b-port outputs (20	J70 (U 0U70)	Fast	1.1	ns
4-	Fall time, B-port outputs (80°	2/ to 200/)	Slow		20
t _f	raii time, b-port outputs (80°	70 (U 2U 70)	Fast	2.6	ns

[†] Slow (ERC = H) and Fast (ERC = L)

 $[\]ddagger$ All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74GTLP2033DGGR	ACTIVE	TSSOP	DGG	48	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GTLP2033	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 11-Mar-2017

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74GTLP2033DGGR	TSSOP	DGG	48	2000	330.0	24.4	8.6	13.0	1.8	12.0	24.0	Q1

www.ti.com 11-Mar-2017



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74GTLP2033DGGR	TSSOP	DGG	48	2000	367.0	367.0	45.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (https://www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2021, Texas Instruments Incorporated